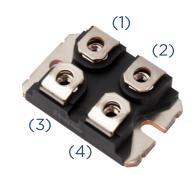
N3T200MP330S 3300 V 200 mΩ Silicon Carbide MOSFET

State-of-the-art SiC MOSFET technology

V_{DS}	I _D	R _{DS(on)}	Package
3300 V	20 A	200 mΩ	SOT-227

(4) G D (1) (2) KS S (3)



Benefits

Features

Higher system efficiency

Reliable gate oxide process100% avalanche tested

Electrically isolated baseplate

- Reduced cooling requirements
- Increased power density
- Increased system switching frequency
- Enhanced system reliability
- Reduced total harmonic distortion

Applications

- Motor drives
- Solar PV inverters
- EV onboard chargers
- · Server power supplies
- Energy storage systems
- EV fast charging stations
- · Solid-state power controllers
- Uninterruptible power supplies

Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	Note
Drain-Source Voltage	V _{(BR)DSS}	T _C = 25 ° C	3300	-	1	٧	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 0 V, V_{GS} = 0 V$	-	1	100	μΑ	Fig. 6
Gate-Source Voltage	V _{GS(max)}		-10	1	25	V	
	$V_{\rm GS,op}$	Recommended Operation	-	-5/+20	ı		
Gate Threshold Voltage	V _{GS(th)}	$V_{GS} = V_{DS}$, $I_D = 2.5$ mA	2	2.64	3	>	Fig. 4
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 20 V, T _C = 25 °C	-	200	ı	mΩ	Fig.
Continuous Drain Current	I _D	V _{GS} = 20 V, T _C = 25 °C	-	20	ı	Α	
Diode Forward Voltage	V _{SD}	V _{GS} = -5 V, I _{SD} = 10 A	-	5	ı	V	Fig. 5

NOVEL MATERIALS AND INNOVATIVE SEMICONDUCTORS

Typical Performance

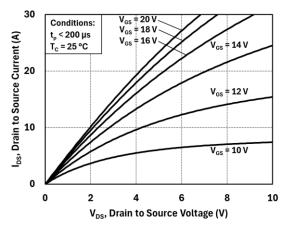


Figure 1: Output Characteristics at 25 °C

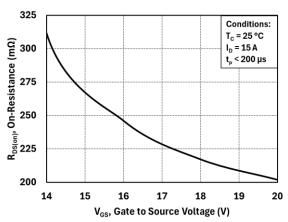


Figure 3: On-Resistance vs. Gate Voltage

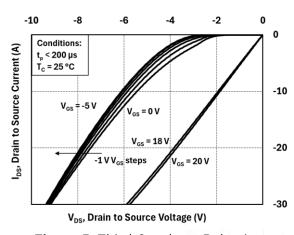


Figure 5: Third Quadrant Behavior

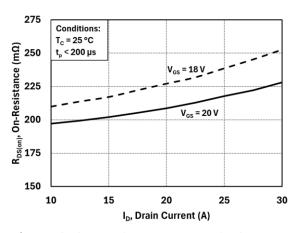


Figure 2: On-Resistance vs. Drain Current

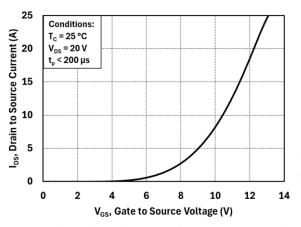


Figure 4: Transfer Characteristics

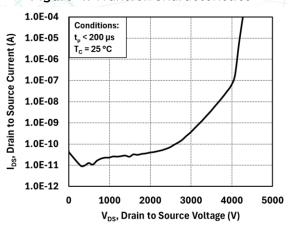


Figure 6: Blocking Behavior

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